

**EAST Search History****EAST Search History (Prior Art)**

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	(support or wafer or carrier or substrate or base) same conductor and (insulat\$4 or oxide or dielectric) same ((copper or "Cu") near foil) and (press\$4 same ((copper or "Cu") near foil)) same (insulat\$4 or oxide or dielectric) and pressuriz\$4 and (b near stage) and (plating or electroplating) same conductor and (438/624,778.ccls.)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/29 12:42
L2	1	(support or wafer or carrier or substrate or base) same conductor and (insulat\$4 or oxide or dielectric) same ((copper or "Cu") near foil) and (press\$4 same ((copper or "Cu") near foil)) same (insulat\$4 or oxide or dielectric) and pressuriz\$4 and (b near stage) and (plating or electroplating) same conductor and gotoh . inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/29 12:45
S1	0	("JP2001-537286") or ("JP2001-68850") or ("JP7-111375") or ("JP6-350258") or ("JP10-022636") or ("JP2002-137328") or ("JP2002-134881") or ("JP2002-076578")). PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/06/26 09:27

S2	37	"5600103"	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/26 10:34
S3	172	"power supply film"	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/26 10:34
S4	1	"power supply film" and insulat\$4 and conduct\$4 and "b- stage"	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/26 10:36
S5	4	"power supply film" and insulat\$4 and conduct\$4 and thermoset\$4	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/26 10:36
S6	3	"power supply film" and insulat\$4 and conduct\$4 and thermoset\$4 and curing	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/26 10:37
S7	4	"power supply film" and insulat\$4 and conduct\$4 and thermoset\$4 and cur \$3	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/26 10:37
S8	623590	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base))	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 08:43
S9	239119	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 08:44

S10	16737	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (press \$3 near9 (oxide or dielectric insulat\$4))	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 08:47
S11	381	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (press \$3 near9 (oxide or dielectric insulat\$4)) and ( b near stage)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 08:48
S12	52	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (press \$3 near9 (oxide or dielectric insulat\$4)) and ( b near stage) and (power near supply)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 09:45
S13	27	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (press \$3 near9 (oxide or dielectric insulat\$4)) and ( b near stage) and (power near supply) and (support or frame)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 09:50

S14	11	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (press \$3 near9 (oxide or dielectric insulat\$4)) and ( b near stage) and (power near supply) and (support or frame) and (plating near9 conduct\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 10:12
S15	3	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (pressing near9 (oxide or dielectric insulat\$4)) and ( b near stage) and (power near supply) and (support or frame) and (plating near9 conduct\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 10:13
S16	1982	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (pressing near9 (oxide or dielectric insulat\$4))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 10:14
S17	937	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (pressing near9 (oxide or dielectric insulat\$4)) and (support or frame)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 10:14

S18	86	(conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (pressing near9 (oxide or dielectric insulat\$4)) and (support or frame) and (b near stage)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 10:15
S19	81	((conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (pressing near9 (oxide or dielectric insulat\$4)) and (support or frame) and (b near stage) and ((heat\$4 or thermal) near9 (oxide or dielectric or insulat \$4)))	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/06 09:57
S20	3	((conduct\$4 near9 (semiconductor or wafer or substrate or carrier or base)) and ((insulat\$4 or oxide or dielectric) near9 conduct\$4) and (pressing near9 (oxide or dielectric insulat\$4)) and (support or frame) and (b near stage) and ((heat\$4 or thermal) near9 (oxide or dielectric or insulat \$4)) and (power near supply))	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/02 10:21
S21	128560	(conduct\$4 near9 (plating or etch\$4))	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/24 14:37

S22	111747	(conduct\$4 near9 (plating or etch\$4)) and (support or base pr carrier or arm or substrate or wafer)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/24 14:38
S23	35038	(conduct\$4 near9 (plating or etch\$4)) and (support or base pr carrier or arm or substrate or wafer) and press\$4 and (insulat\$4 or dielectric or oxide) near9 (support or base pr carrier or arm or substrate or wafer)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/24 14:40
S24	7011	(conduct\$4 near9 (plating or etch\$4)) and (support or base pr carrier or arm or substrate or wafer) and press\$4 and (insulat\$4 or dielectric or oxide) near9 (support or base pr carrier or arm or substrate or wafer) and (press\$4 near9 (insulat\$4 or dielectric or oxide))	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/24 14:41
S25	7010	(conduct\$4 near9 (plating or etch\$4)) and (support or base or carrier or arm or substrate or wafer) and press\$4 and (insulat\$4 or dielectric or oxide) near9 (support or base or carrier or arm or substrate or wafer) and (press\$4 near9 (insulat\$4 or dielectric or oxide))	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/24 14:42

S26	338	(conduct\$4 near9 (plating or etch\$4)) and (support or base or carrier or arm or substrate or wafer) and press\$4 and (insulat\$4 or dielectric or oxide) near9 (support or base or carrier or arm or substrate or wafer) and (press\$4 near9 (insulat\$4 or dielectric or oxide)) and (electronic near part)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/24 14:44
S27	46	(conduct\$4 near9 (plating or etch\$4)) and (support or base or carrier or arm or substrate or wafer) and press\$4 and (insulat\$4 or dielectric or oxide) near9 (support or base or carrier or arm or substrate or wafer) and (press\$4 near9 (insulat\$4 or dielectric or oxide)) and (electronic near part) and (B near stage)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/24 15:01
S28	88010	(conduct\$4 near portion)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/26 09:55
S29	12774	(conduct\$4 near portion) near9 (support or base or substrate or wafer)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/26 10:52
S30	1242	(conduct\$4 near portion) near9 (support or base or substrate or wafer) and (copper near9 (insulat\$4 or oxide or dielectric))	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/26 10:54

S31	55	(conduct\$4 near portion) near9 (support or base or substrate or wafer) and (copper near9 (insulat\$4 or oxide or dielectric)) and (b near stage)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/26 10:54
S32	46	(conduct\$4 near portion) near9 (support or base or substrate or wafer) and (copper near9 (insulat\$4 or oxide or dielectric)) and (b near stage) and press \$4	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/26 10:55
S33	27	(conduct\$4 near portion) near9 (support or base or substrate or wafer) and (copper near9 (insulat\$4 or oxide or dielectric)) and (b near stage) and press \$4 and thermoplastic	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/26 10:56
S34	25	(conduct\$4 near portion) near9 (support or base or substrate or wafer) and (copper near9 (insulat\$4 or oxide or dielectric)) and (b near stage) and press \$4 and thermoplastic and (heat or anneal)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/26 10:56
S35	9	(conduct\$4 near portion) near9 (support or base or substrate or wafer) and (copper near9 (insulat\$4 or oxide or dielectric)) and (b near stage) and press \$4 and thermoplastic and (heat or anneal) and (power near supply)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/26 10:56

S36	7	("5480048"   "5600103"   "5970319"   "6930388").PN. and (conduct\$4 or metal) with (substrate or wafer or carrier or base or plate or support)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/07 09:30
S37	2	("5480048"   "5600103"   "5970319"   "6930388").PN. and (conduct\$4 or metal) with (substrate or wafer or carrier or base or plate or support) and (insulat\$4 or oxide or dielectric) and press\$4 with (insulat\$4 or oxide or dielectric)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/07 09:32
S38	380505	(support or wafer or carrier or substrate or base) same conductor	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/06 09:52
S39	4336	((support or wafer or carrier or substrate or base) same conductor and (insulat\$4 or oxide or dielectric) same ((copper or "Cu") near foil)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/06 09:53
S40	1442	((support or wafer or carrier or substrate or base) same conductor and (insulat\$4 or oxide or dielectric) same ((copper or "Cu") near foil) and (press\$4 same ((copper or "Cu") near foil))	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/06 09:54

S41	1137	(support or wafer or carrier or substrate or base) same conductor and (insulat\$4 or oxide or dielectric) same ((copper or "Cu") near foil) and (press\$4 same ((copper or "Cu") near foil)) same (insulat\$4 or oxide or dielectric)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/06 09:56
S42	118	(support or wafer or carrier or substrate or base) same conductor and (insulat\$4 or oxide or dielectric) same ((copper or "Cu") near foil) and (press\$4 same ((copper or "Cu") near foil)) same (insulat\$4 or oxide or dielectric) and pressuriz\$4	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/06 10:04
S43	56	(support or wafer or carrier or substrate or base) same conductor and (insulat\$4 or oxide or dielectric) same ((copper or "Cu") near foil) and (press\$4 same ((copper or "Cu") near foil)) same (insulat\$4 or oxide or dielectric) and pressuriz\$4 and (b near stage)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/06 10:04
S44	49	(support or wafer or carrier or substrate or base) same conductor and (insulat\$4 or oxide or dielectric) same ((copper or "Cu") near foil) and (press\$4 same ((copper or "Cu") near foil)) same (insulat\$4 or oxide or dielectric) and pressuriz\$4 and (b near stage) and (plating or	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/06 10:05

		electroplating)				
S45	23	(support or wafer or carrier or substrate or base) same conductor and (insulat\$4 or oxide or dielectric) same ((copper or "Cu") near foil) and (press\$4 same ((copper or "Cu") near foil)) same (insulat\$4 or oxide or dielectric) and pressuriz\$4 and (b near stage) and (plating or electroplating) same conductor	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/06 10:05
S46	2	"7237332".pn.	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/16 07:59
S47	2	"5049221".pn.	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/16 08:11
S48	0	(support or wafer or carrier or substrate or base) same conductor and (insulat\$4 or oxide or dielectric) same ((copper or "Cu") near foil) and (press\$4 same ((copper or "Cu") near foil)) same (insulat\$4 or oxide or dielectric) and pressuriz\$4 and (b near stage) and (plating or electroplating) same conductor and 438/624.cols.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/16 08:22
S49	7	438/624.cols. and (b near stage)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/16 08:22

S50	7	438/624.ccls. and (b near stage) and (substrate or wafer or carrier or base or plate)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/16 08:23
S51	1	438/624.ccls. and (b near stage) and (substrate or wafer or carrier or base or plate) and thermo	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/16 08:35
S52	2	"5480048".pn.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/03/16 08:38

**EAST Search History (Interference)**

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	9	(support or wafer or carrier or substrate or base) same conductor and (insulat\$4 or oxide or dielectric) same ((copper or "Cu") near foil) and (press\$4 same ((copper or "Cu") near foil)) same (insulat\$4 or oxide or dielectric) and pressuriz\$4 and (b near stage) and (plating or electroplating) same conductor .clm.	US_PGPUB; USPAT	OR	ON	2009/07/29 12:45

7/29/09 1:02:13 PM

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